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MOSFET - Power, Dual N- & P-Channel, μ8FL

100 V, 70 mΩ, 9.5 A, -100 V, 186 mΩ, -5 A

NTTBC070NP10M5L

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Features

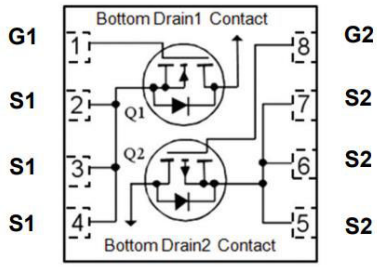
- Small Footprint (3 x 3 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

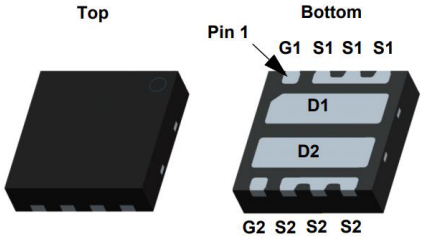
Typical Applications

- Power Tools, Battery Operated Vacuums
- UAV/Drones, Material Handling
- Motor Drive, Home Automation

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
100 V	70 mΩ @ 10 V	9.5 A
−100 V	186 mΩ @ 10 V	−5 A

Dual−Channel MOSFET





μ8FL
CASE 511DG

MAXIMUM RATINGS (T_J = 25°C, Unless otherwise specified)

Parameter			Symbol	Q1	Q2	Unit
Drain−to−Source Breakdown Voltage			$V_{(BR)DSS}$	100	−100	V
Gate−to−Source Voltage			V_{GS}	±20	±20	V
Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	T_C = 25°C	I_D	9.5	−5	A
Power Dissipation $R_{\theta JC}$ (Note 2)			P_D	14	10	W
Continuous Drain Current $R_{\theta JA}$ (Note 1, 2)	Steady State	T_A = 25°C	I_D	3.5	−2.2	A
Power Dissipation $R_{\theta JA}$ (Note 1, 2)			P_D	1.9	1.9	W
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	33	33	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	−55 to +150		°C
Source Current (Body Diode)			I_S	12	8	A
Single Pulse Drain−to−Source Avalanche Energy (I_L = 7.3 A, 7.8 A, L = 1 mH)			E_{AS}	26	30	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)			T_L	260	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface−mounted on FR4 board using 1 in^2 pad size, 1 oz Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

MARKING DIAGRAM

&Y = ON Semiconductor Logo
&Z = Assembly Plant Code
&2 = Numeric Date Code
&K = Lot Code
70NP10M5L = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 10 of this data sheet.

THERMAL CHARACTERISTICS

Symbol	Parameter	Q1	Q2	Unit
$R_{\theta JC}$	Junction−to−Case − Steady State (Note 3)	8.9	12.5	°C/W
$R_{\theta JA}$	Junction−to−Ambient − Steady State (Note 3)	65	65	

3. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

ELECTRICAL CHARACTERISTICS (Q1, N−CHANNEL) (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		100			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}$ / T_J	I_D = 250 μA, ref to 25°C			70		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 100 V	T_J = 25°C			1	μA
			T_J = 125°C			100	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 24 μA		1.0		3.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}$ / T_J	I_D = 24 μA, ref to 25°C			7.1		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 1.3A			47	70	mΩ
		V_{GS} = 4.5 V, I_D = 1.0 A			67	102	
Forward Transconductance	g_{FS}	V_{DS} = 5 V, I_D = 4 A			6.2		S
Gate−Resistance	R_G	T_A = 25°C			0.74		Ω
CHARGES & CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 50 V			252		pF
Output Capacitance	C_{OSS}				64		
Reverse Transfer Capacitance	C_{RSS}				3		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 50 V, I_D = 1.3 A			3		nC
Threshold Gate Charge	$Q_{G(TH)}$				0.6		
Gate−to−Source Charge	Q_{GS}				1.0		
Gate−to−Drain Charge	Q_{GD}				1.1		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DD} = 50 V, I_D = 1.3 A			5.6		
Plateau Voltage	V_{GP}				2.6		V
SWITCHING CHARACTERISTICS							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 10 V, V_{DS} = 50 V, I_D = 1.3 A, R_G = 6 Ω			5.3		ns
Rise Time	t_r				2.5		
Turn−Off Delay Time	$t_{d(OFF)}$				12.4		
Fall Time	t_f				7.5		
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DS} = 50 V, I_D = 1.3 A, R_G = 6 Ω			7.6		ns
Rise Time	t_r				7.6		
Turn−Off Delay Time	$t_{d(OFF)}$				10.4		
Fall Time	t_f				9		

ELECTRICAL CHARACTERISTICS (Q1, N−CHANNEL) (T_J = 25°C unless otherwise noted) (continued)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 1.3 A	T_J = 25°C		0.75	1.2	V
			T_J = 125°C		0.6		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 50 A/μs, I_S = 1.2 A			28		ns
Charge Time	t_a				13		
Discharge Time	t_b				15		
Reverse Recovery Charge	Q_{RR}				8		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ELECTRICAL CHARACTERISTICS (Q2, P−CHANNEL) (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA		−100			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}$ / T_J	I_D = −250 μA, ref to 25°C			60		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = −100 V	T_J = 25°C			−1	μA
			T_J = 125°C			−100	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −40 μA		−2.0		−4.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}$ / T_J	I_D = −40 μA, ref to 25°C			6.6		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = −10 V, I_D = −2.2 A			146	186	mΩ
		V_{GS} = −6 V, I_D = −1.4 A			178	284	
Forward Transconductance	g_{FS}	V_{DS} = 5 V, I_D = −4 A			5.9		S
Gate−Resistance	R_G	T_A = 25°C			1.75		Ω
CHARGES & CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = −50 V			256		pF
Output Capacitance	C_{OSS}				63		
Reverse Transfer Capacitance	C_{RSS}				3		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −10 V, V_{DS} = −50 V, I_D = −2.2 A			7.3		nC
Threshold Gate Charge	$Q_{G(TH)}$				1.5		
Gate−to−Source Charge	Q_{GS}				2.4		
Gate−to−Drain Charge	Q_{GD}				1.2		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −6 V, V_{DD} = −50 V, I_D = −2.2 A			4.6		nC
Plateau Voltage	V_{GP}				4.5		V
SWITCHING CHARACTERISTICS							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −10 V, V_{DS} = −50 V, I_D = −2.2 A, R_G = 6 Ω			8.9		ns
Rise Time	t_r				3.6		
Turn−Off Delay Time	$t_{d(OFF)}$				13.2		
Fall Time	t_f				3.4		

ELECTRICAL CHARACTERISTICS (Q2, P−CHANNEL) (T_J = 25°C unless otherwise noted) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −6 V, V_{DS} = −50 V, I_D = −2.2 A, R_G = 6 Ω		10.8		ns
Rise Time	t_r			4.8		
Turn−Off Delay Time	$t_{d(OFF)}$			10		
Fall Time	t_f			4.1		

OFF CHARACTERISTICS

Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −2.2 A, T_J = 25°C		−0.86	−1.2	V
		T_J = 125°C		−0.72		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = −1.1 A		34		ns
Charge Time	t_a			27		
Discharge Time	t_b			7		
Reverse Recovery Charge	Q_{RR}			53		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS – N–CHANNEL

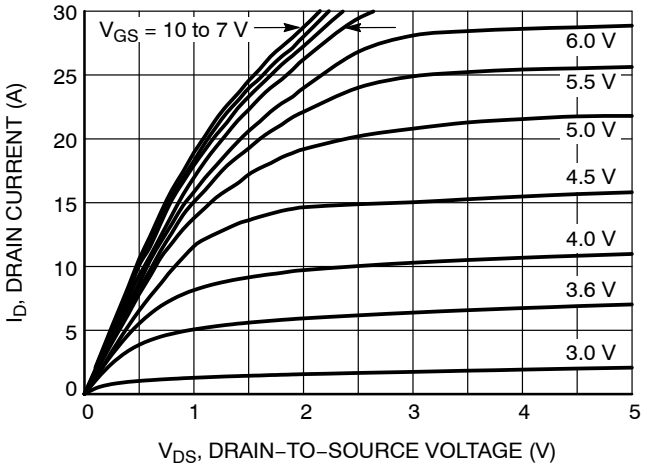


Figure 1. On–Region Characteristics

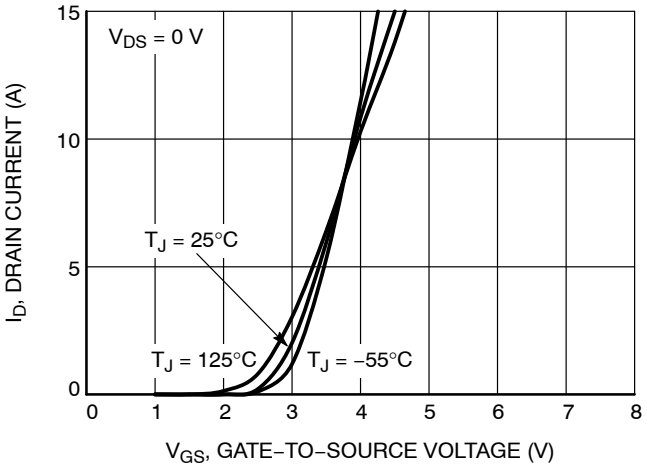


Figure 2. Transfer Characteristics

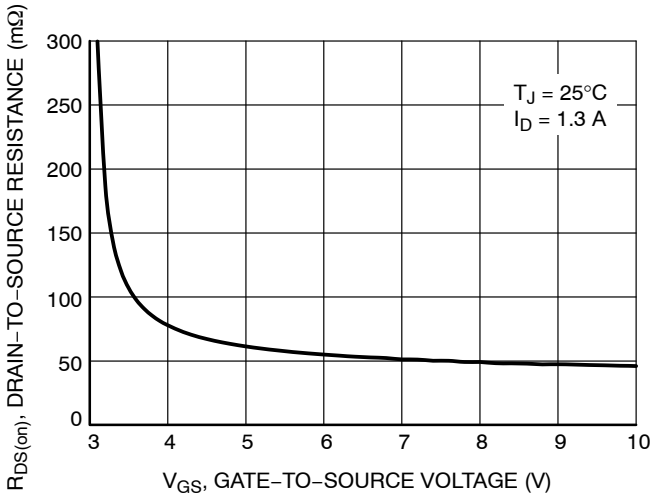


Figure 3. On–Resistance vs. Gate–to–Source Voltage

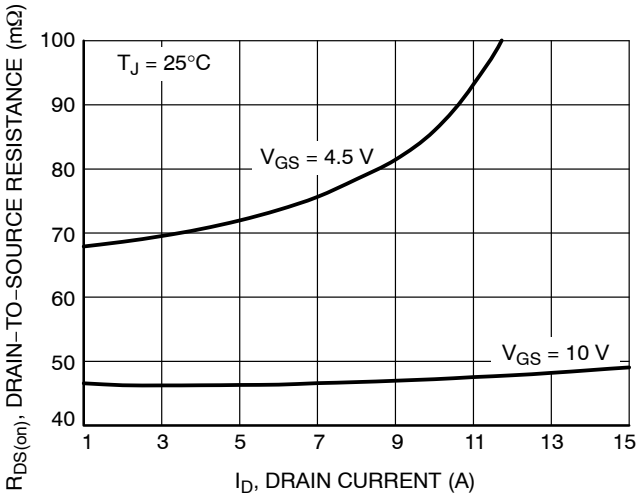


Figure 4. On–Resistance vs. Drain Current

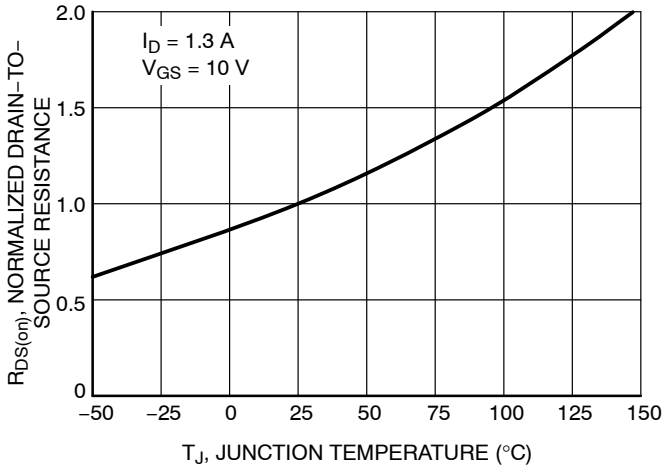


Figure 5. On–Resistance Variation with Temperature

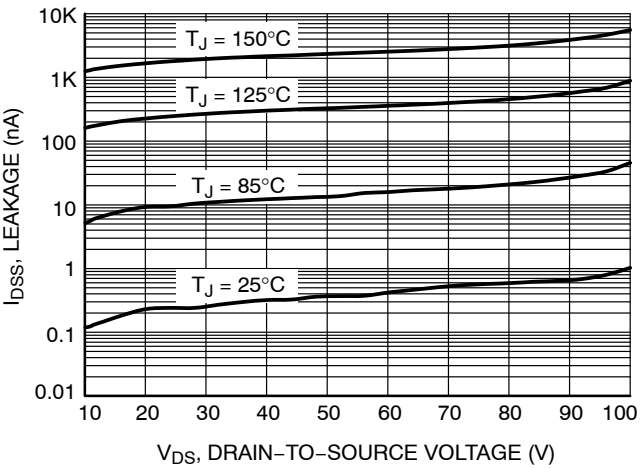


Figure 6. Drain–to–Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS – N–CHANNEL

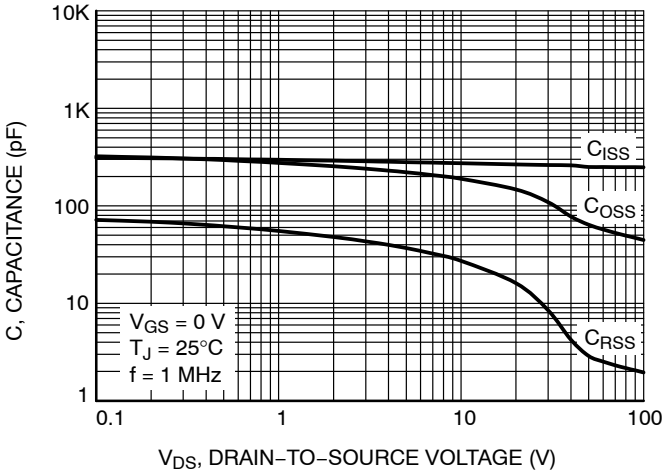


Figure 7. Capacitance Variation

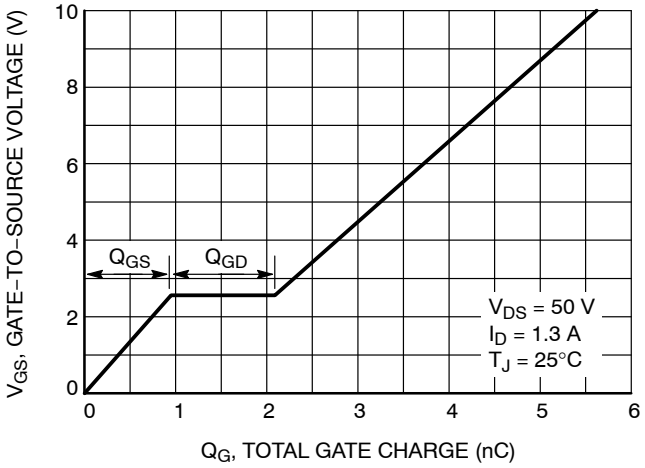


Figure 8. Gate–to–Source Voltage vs. Total Charge

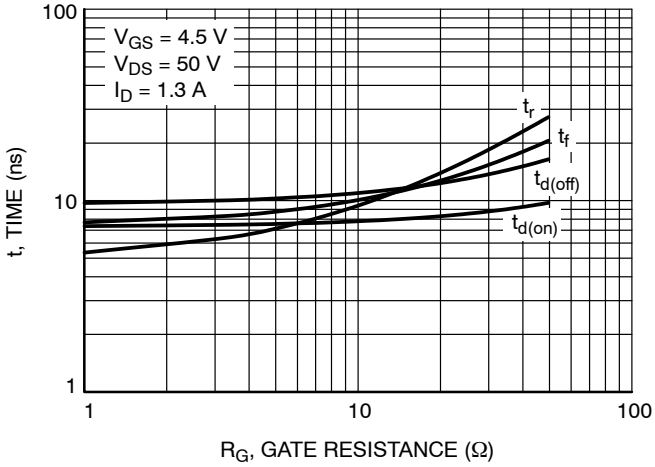


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

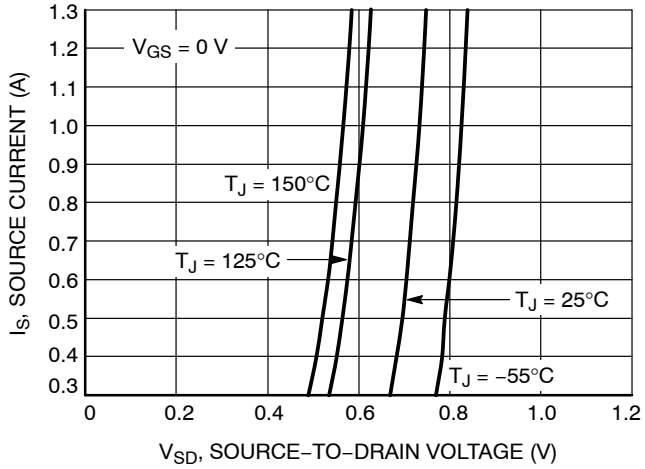


Figure 10. Diode Forward Voltage vs. Current

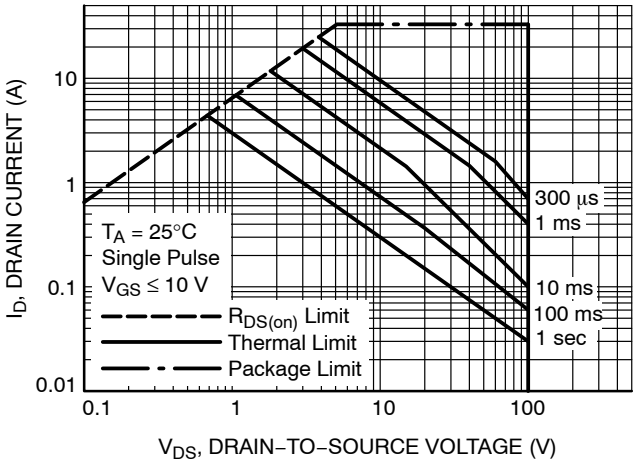


Figure 11. Safe Operating Area

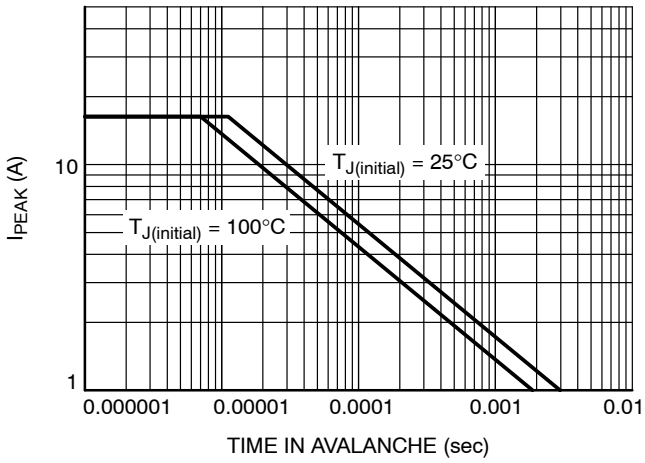


Figure 12. I_{PEAK} vs. Time in Avalanche

TYPICAL CHARACTERISTICS – N–CHANNEL

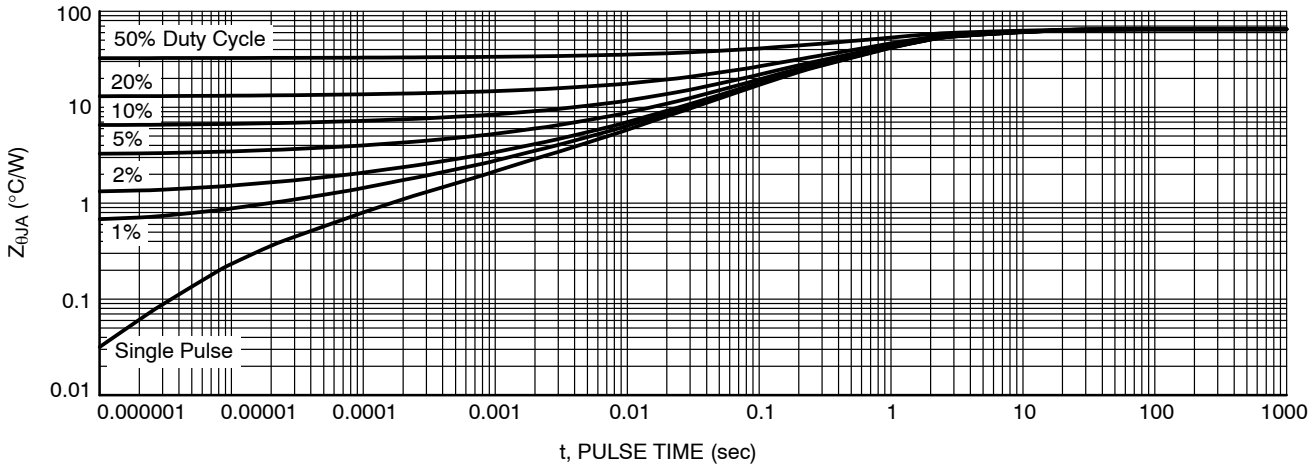


Figure 13. Junction–to–Ambient Transient Thermal Response

TYPICAL CHARACTERISTICS – P–CHANNEL

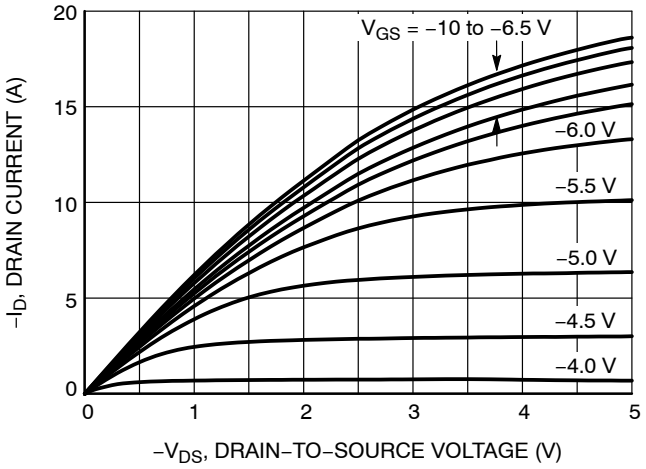


Figure 14. On−Region Characteristics

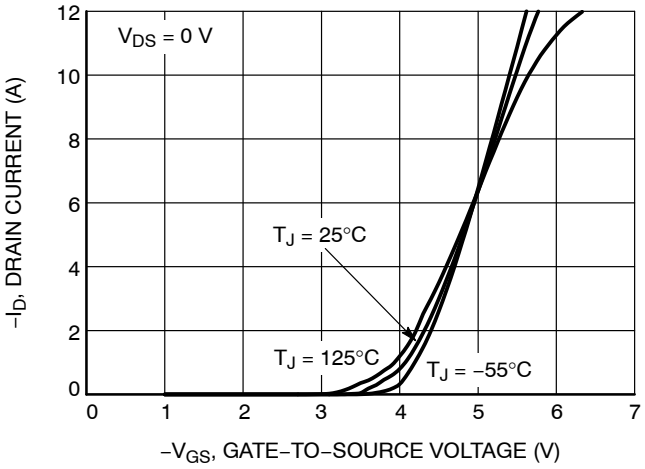


Figure 15. Transfer Characteristics

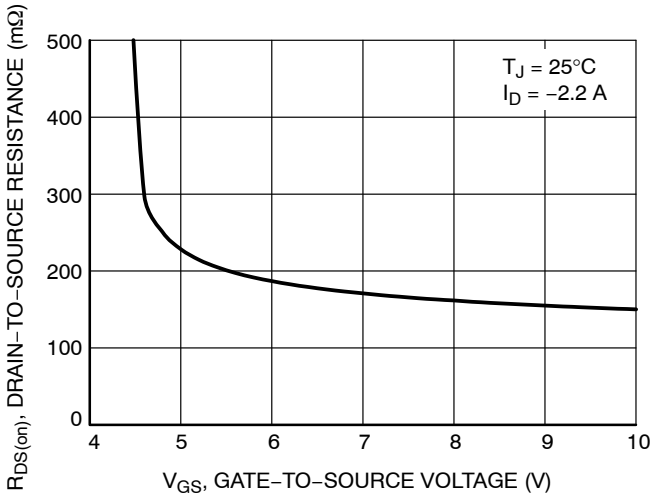


Figure 16. On−Resistance vs. Gate−to−Source Voltage

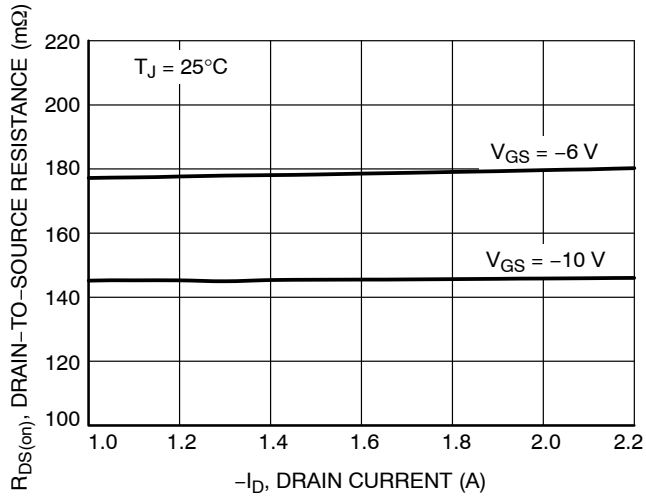


Figure 17. On−Resistance vs. Drain Current

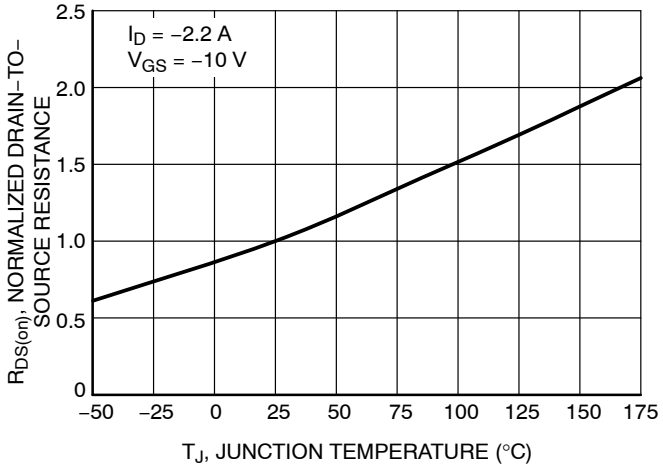


Figure 18. On−Resistance Variation with Temperature

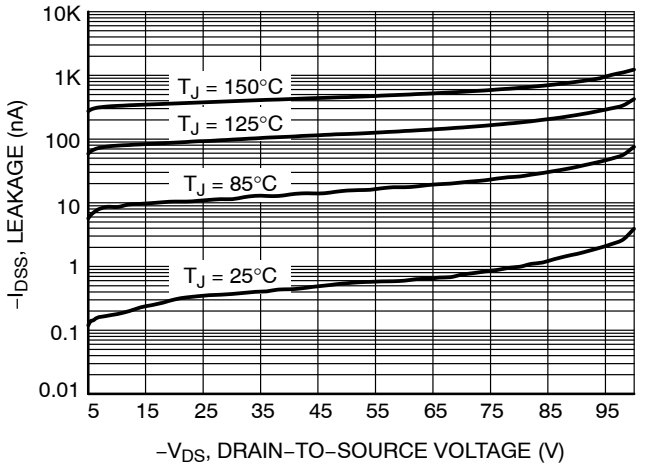


Figure 19. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS – P–CHANNEL

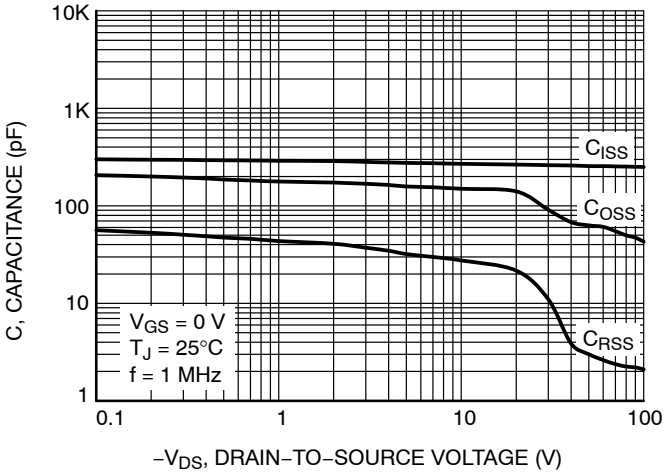


Figure 20. Capacitance Variation

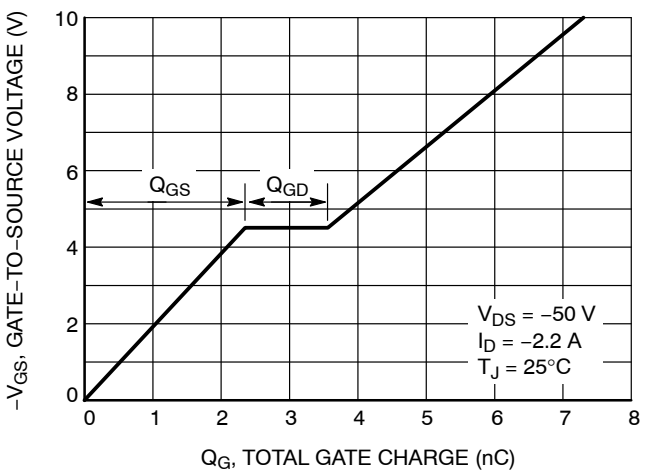


Figure 21. Gate–to–Source Voltage vs. Total Charge

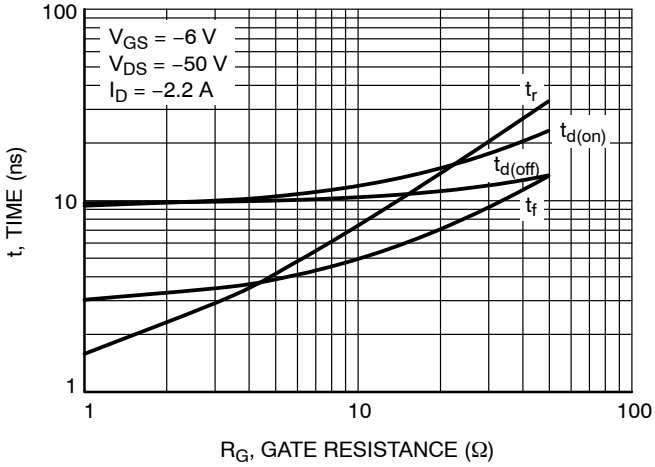


Figure 22. Resistive Switching Time Variation vs. Gate Resistance

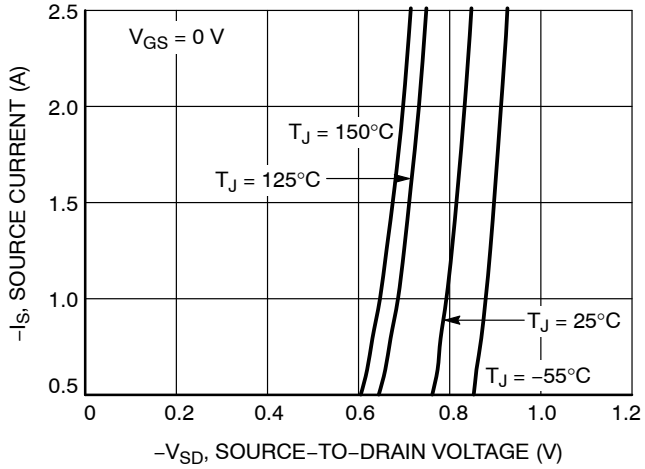


Figure 23. Diode Forward Voltage vs. Current

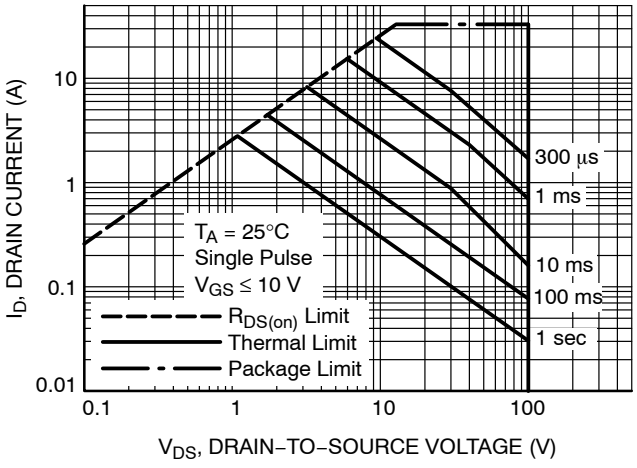


Figure 24. Safe Operating Area

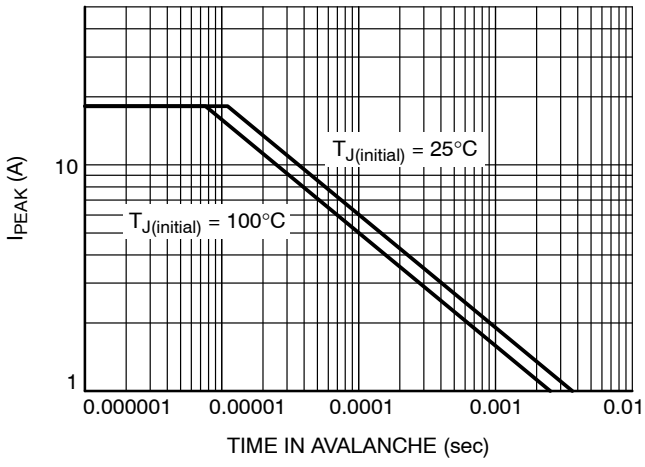


Figure 25. I_{PEAK} vs. Time in Avalanche

TYPICAL CHARACTERISTICS − P−CHANNEL

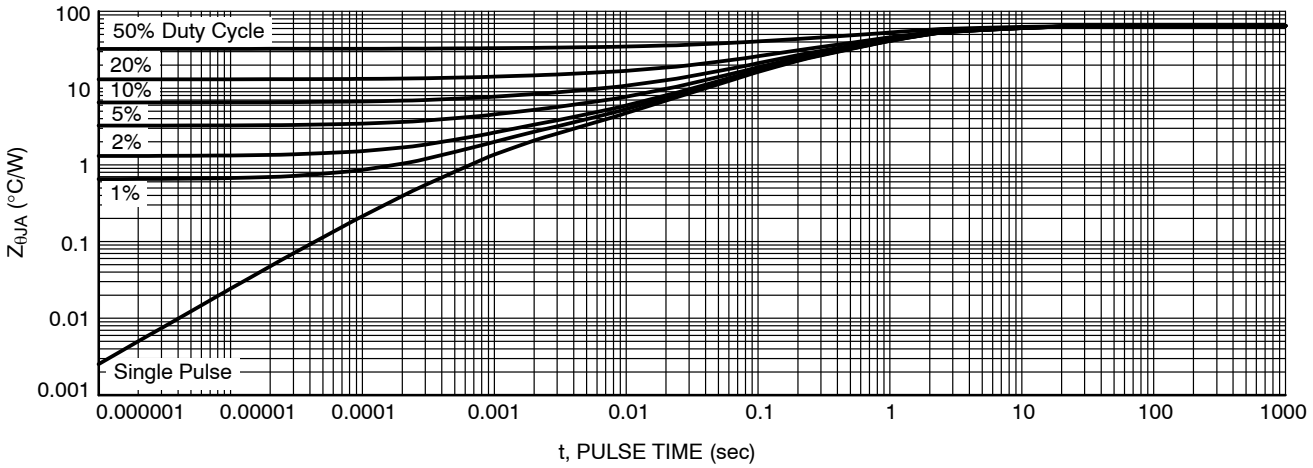


Figure 26. Junction−to−Ambient Transient Thermal Response

ORDERING INFORMATION

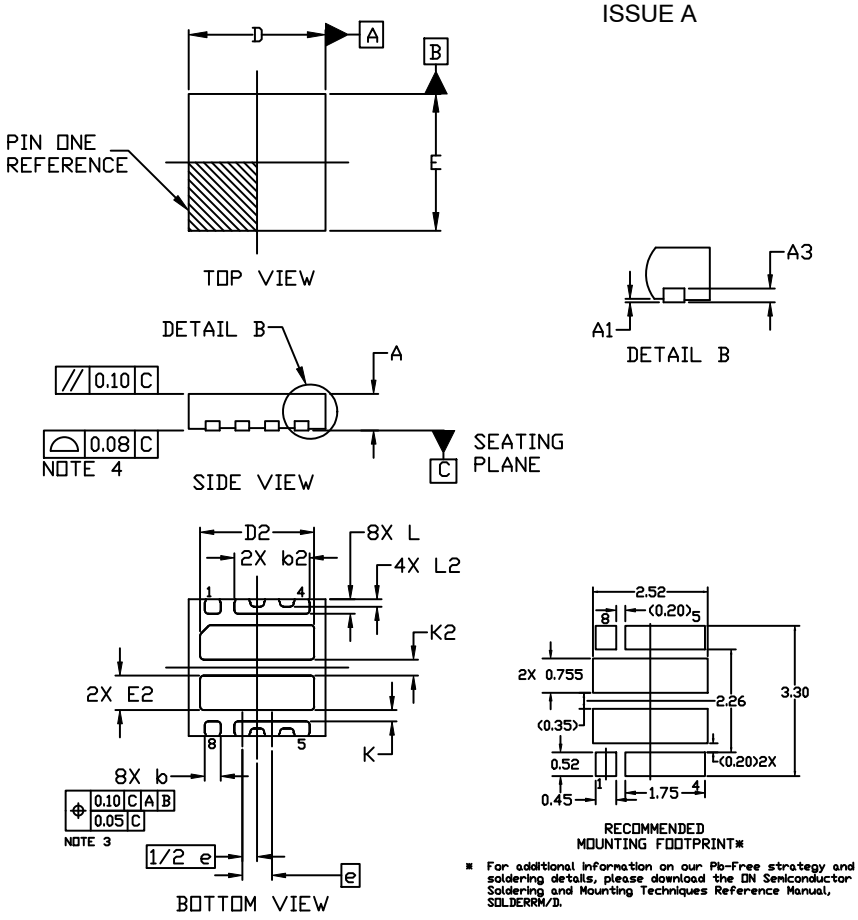
Device	Device Marking	Package	Shipping (Qty / Packing)†
NTTBC070NP10M5L	70NP10M5L	μ8FL (Pb−Free/Halogen Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTTBC070NP10M5L

PACKAGE DIMENSIONS

WDFN8 3x3, 0.65P
CASE 511DG
ISSUE A



* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO PLATED TERMINALS AND IS MEASURED BETWEEN 0.15 AND 0.30MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	---	0.05
A3		0.20 REF	
b	0.30	0.35	0.40
b2		1.65 REF	
D	2.90	3.00	3.10
D2	2.45	2.50	2.55
E	2.90	3.00	3.10
E2	1.40	1.50	1.60
e		0.65 BSC	
K	0.25	---	---
K2		0.35 REF	
L	0.27	0.32	0.37
L2		0.163 REF	

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